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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	147
Number of Gates	199000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epf10k50sqc208-1

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

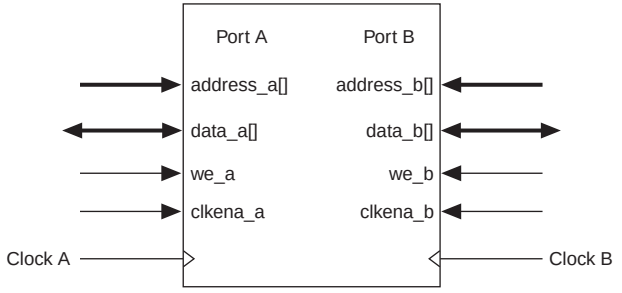
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

The EAB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 3.

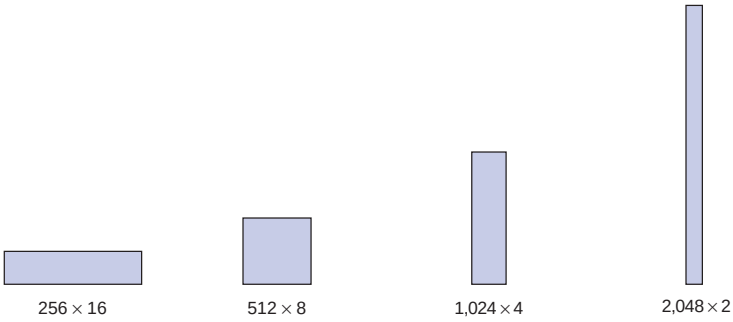
Figure 3. FLEX 10KE EAB in Dual-Port RAM Mode



The FLEX 10KE EAB can be used in a single-port mode, which is useful for backward-compatibility with FLEX 10K designs (see Figure 4).

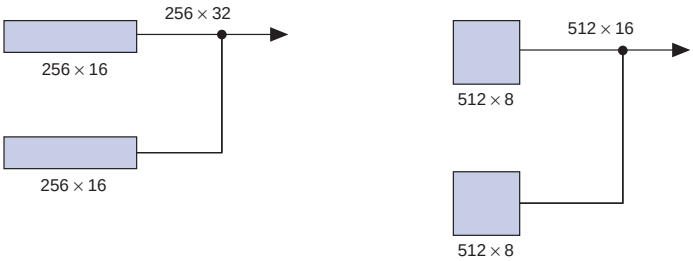
When used as RAM, each EAB can be configured in any of the following sizes: 256 × 16, 512 × 8, 1,024 × 4, or 2,048 × 2 (see Figure 5).

Figure 5. FLEX 10KE EAB Memory Configurations



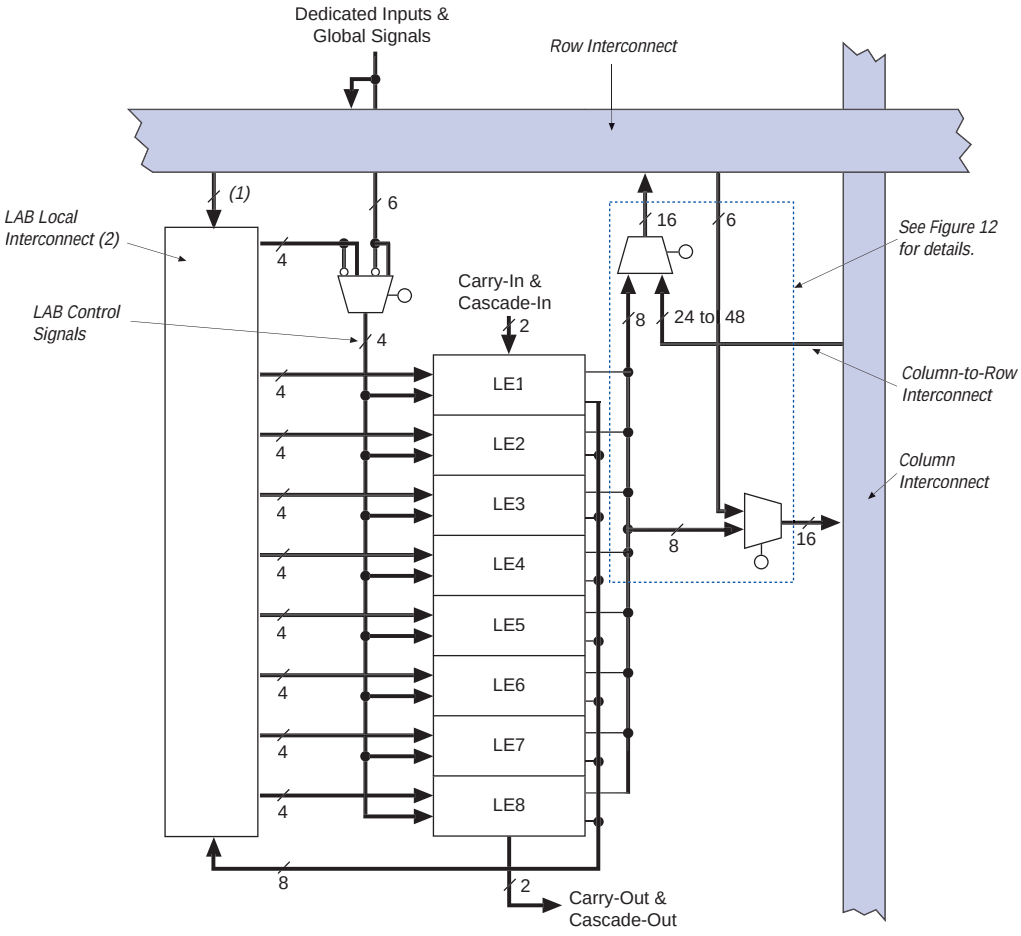
Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 16 RAM blocks can be combined to form a 256 × 32 block; two 512 × 8 RAM blocks can be combined to form a 512 × 16 block (see Figure 6).

Figure 6. Examples of Combining FLEX 10KE EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. The Altera software automatically combines EABs to meet a designer's RAM specifications.

Figure 7. FLEX 10KE LAB



Notes:

(1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 22 inputs to the LAB local interconnect channel from the row; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 26.

(2) EPF10K30E, EPF10K50E, and EPF10K50S devices have 30 LAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 34.

Figure 13. FLEX 10KE LAB Connections to Row & Column Interconnect

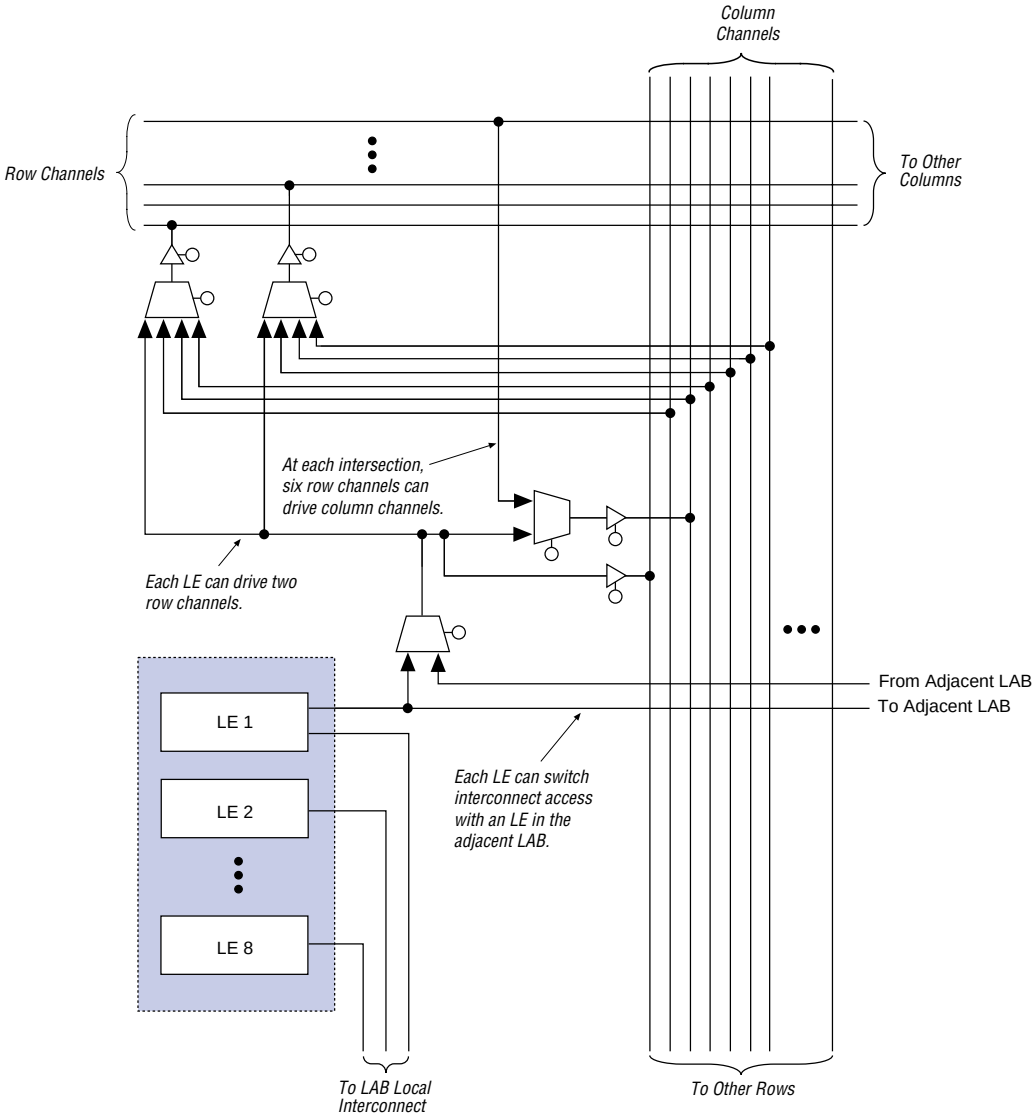
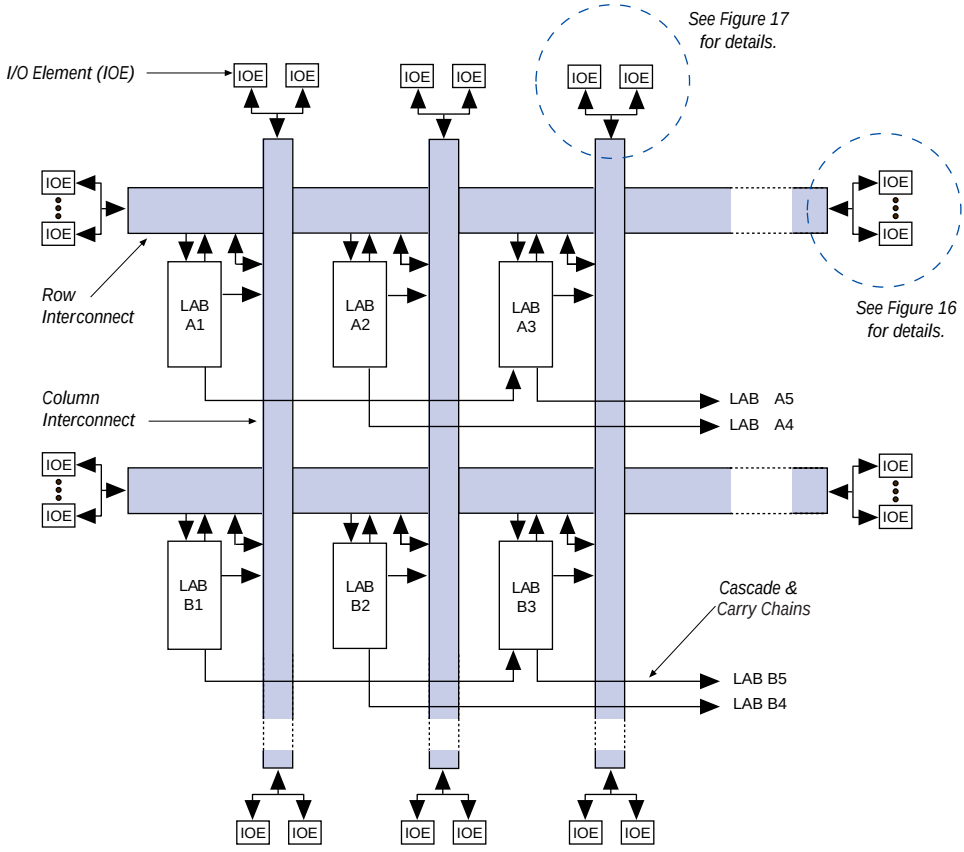


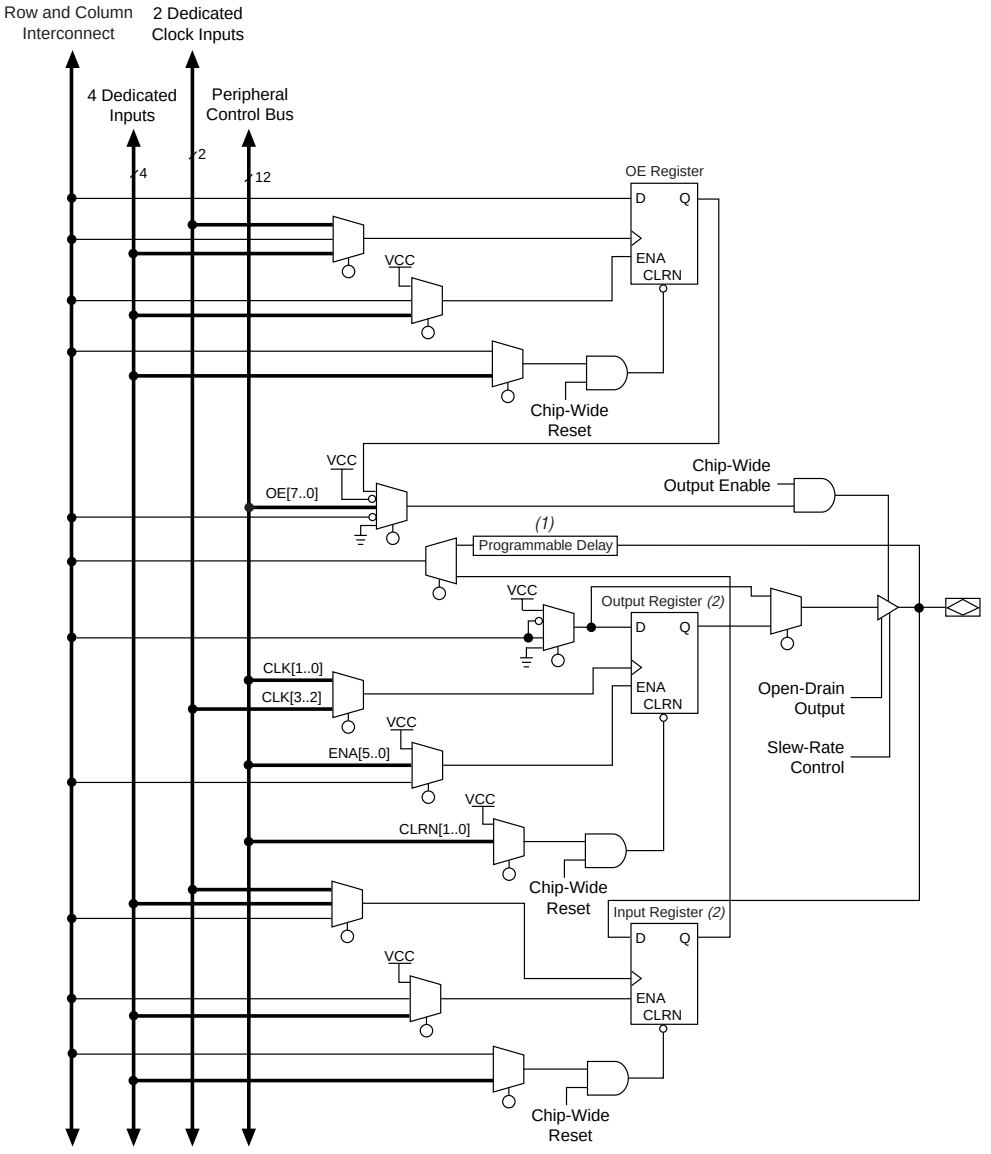
Figure 14. FLEX 10KE Interconnect Resources



I/O Element

An IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data that requires a fast setup time, or as an output register for data that requires fast clock-to-output performance. In some cases, using an LE register for an input register will result in a faster setup time than using an IOE register. IOEs can be used as input, output, or bidirectional pins. For bidirectional registered I/O implementation, the output register should be in the IOE, and the data input and output enable registers should be LE registers placed adjacent to the bidirectional pin. The Altera Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Figure 15 shows the bidirectional I/O registers.

Figure 15. FLEX 10KE Bidirectional I/O Registers



Note:

(1) All FLEX 10KE devices (except the EPF10K50E and EPF10K200E devices) have a programmable input delay buffer on the input path.

ClockLock & ClockBoost Features

To support high-speed designs, FLEX 10KE devices offer optional ClockLock and ClockBoost circuitry containing a phase-locked loop (PLL) used to increase design speed and reduce resource usage. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by resource sharing within the device. The ClockBoost feature allows the designer to distribute a low-speed clock and multiply that clock on-device. Combined, the ClockLock and ClockBoost features provide significant improvements in system performance and bandwidth.

All FLEX 10KE devices, except EPF10K50E and EPF10K200E devices, support ClockLock and ClockBoost circuitry. EPF10K50S and EPF10K200S devices support this circuitry. Devices that support ClockLock and ClockBoost circuitry are distinguished with an "X" suffix in the ordering code; for instance, the EPF10K200SFC672-1X device supports this circuit.

The ClockLock and ClockBoost features in FLEX 10KE devices are enabled through the Altera software. External devices are not required to use these features. The output of the ClockLock and ClockBoost circuits is not available at any of the device pins.

The ClockLock and ClockBoost circuitry locks onto the rising edge of the incoming clock. The circuit output can drive the clock inputs of registers only; the generated clock cannot be gated or inverted.

The dedicated clock pin (GCLK1) supplies the clock to the ClockLock and ClockBoost circuitry. When the dedicated clock pin is driving the ClockLock or ClockBoost circuitry, it cannot drive elsewhere in the device.

For designs that require both a multiplied and non-multiplied clock, the clock trace on the board can be connected to the GCLK1 pin. In the Altera software, the GCLK1 pin can feed both the ClockLock and ClockBoost circuitry in the FLEX 10KE device. However, when both circuits are used, the other clock pin cannot be used.

Figure 22 shows the required relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance.

Figure 22. Relationship between V_{CCIO} & V_{CCINT} for 3.3-V PCI Compliance

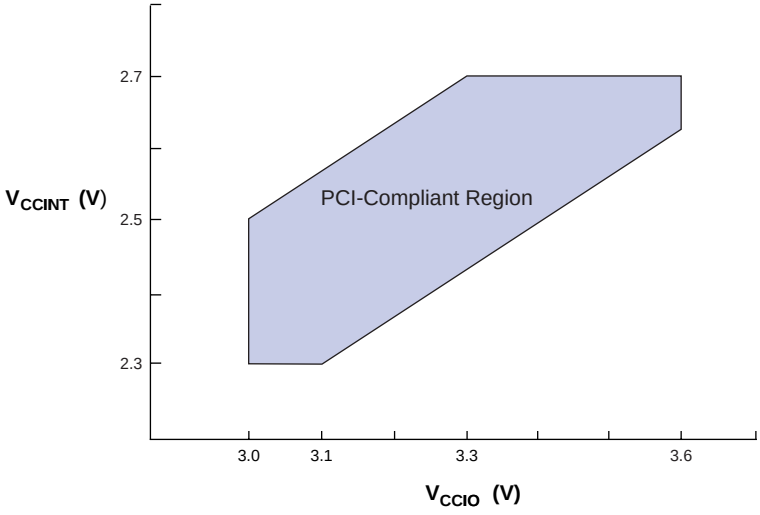


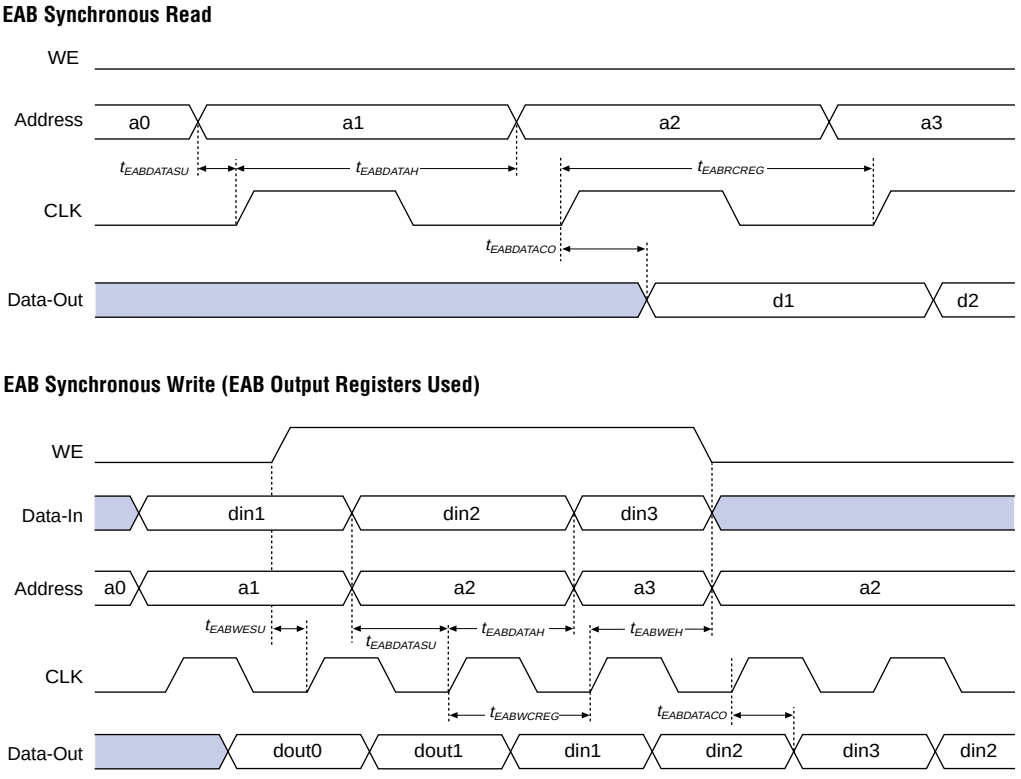
Figure 23 shows the typical output drive characteristics of FLEX 10KE devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compliant to the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (when VCCIO pins are connected to 3.3 V). FLEX 10KE devices with a -1 speed grade also comply with the drive strength requirements of the ***PCI Local Bus Specification, Revision 2.2*** (when VCCINT pins are powered with a minimum supply of 2.375 V, and VCCIO pins are connected to 3.3 V). Therefore, these devices can be used in open 5.0-V PCI systems.

Table 24. LE Timing Microparameters (Part 2 of 2) *Note (1)*		
Symbol	**Parameter**	**Condition**
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 25. IOE Timing Microparameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 27. EAB Timing Macroparameters *Note (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Figure 30. EAB Synchronous Timing Waveforms



Tables 31 through 37 show EPF10K30E device internal and external timing parameters.

Table 31. EPF10K30E Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.1	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.6		0.7		1.0	ns
t_{PACKED}		0.3		0.4		0.5	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.1		0.1		0.2	ns
t_{CGEN}		0.4		0.5		0.7	ns

Table 50. EPF10K100E External Timing Parameters *Notes (1), (2)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	2.0		2.5		3.3		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.2	2.0	6.9	2.0	9.1	ns
t_{INSU} *(4)*	2.0		2.2		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	3.0	0.5	4.6	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 51. EPF10K100E External Bidirectional Timing Parameters *Notes (1), (2)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{INSUBIDIR}$ *(3)*	1.7		2.5		3.3		ns
$t_{INHBIDIR}$ *(3)*	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ *(4)*	2.0		2.8		–		ns
$t_{INHBIDIR}$ *(4)*	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ *(3)*	2.0	5.2	2.0	6.9	2.0	9.1	ns
$t_{XZBIDIR}$ *(3)*		5.6		7.5		10.1	ns
$t_{ZXBIDIR}$ *(3)*		5.6		7.5		10.1	ns
$t_{OUTCOBIDIR}$ *(4)*	0.5	3.0	0.5	4.6	–	–	ns
$t_{XZBIDIR}$ *(4)*		4.6		6.5		–	ns
$t_{ZXBIDIR}$ *(4)*		4.6		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Table 56. EPF10K130E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		2.8		3.5		4.4	ns
t_{DIN2LE}		0.7		1.2		1.6	ns
$t_{DIN2DATA}$		1.6		1.9		2.2	ns
$t_{DCLK2IOE}$		1.6		2.1		2.7	ns
$t_{DCLK2LE}$		0.7		1.2		1.6	ns
$t_{SAMELAB}$		0.1		0.2		0.2	ns
$t_{SAMEROW}$		1.9		3.4		5.1	ns
$t_{SAMECOLUMN}$		0.9		2.6		4.4	ns
$t_{DIFFROW}$		2.8		6.0		9.5	ns
$t_{TWOROWS}$		4.7		9.4		14.6	ns
$t_{LEPERIPH}$		3.1		4.7		6.9	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	1.9		2.1		3.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
t_{INSU} *(4)*	0.9		1.1		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	4.0	0.5	6.0	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 58. EPF10K130E External Bidirectional Timing Parameters Notes (1), (2)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (3)	2.2		2.4		3.2		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (4)	2.8		3.0		–		ns
$t_{INHBIDIR}$ (4)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (3)	2.0	5.0	2.0	7.0	2.0	9.2	ns
$t_{XZBIDIR}$ (3)		5.6		8.1		10.8	ns
$t_{ZXBIDIR}$ (3)		5.6		8.1		10.8	ns
$t_{OUTCOBIDIR}$ (4)	0.5	4.0	0.5	6.0	–	–	ns
$t_{XZBIDIR}$ (4)		4.6		7.1		–	ns
$t_{ZXBIDIR}$ (4)		4.6		7.1		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 59 through 65 show EPF10K200E device internal and external timing parameters.

Table 59. EPF10K200E Device LE Timing Microparameters (Part 1 of 2) Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.2	ns
t_{CLUT}		0.4		0.5		0.6	ns
t_{RLUT}		0.6		0.7		0.9	ns
t_{PACKED}		0.3		0.5		0.7	ns
t_{EN}		0.4		0.5		0.6	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.2		0.2		0.3	ns
t_{CASC}		0.7		0.8		1.2	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.4		0.6		0.8	ns
t_{SU}	0.4		0.6		0.7		ns

Table 61. EPF10K200E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		2.0		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.4		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABBYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.9		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		3.1		3.7		4.9	ns
t_{WP}	3.3		4.0		5.3		ns
t_{RP}	0.9		1.1		1.5		ns
t_{WDSU}	0.9		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.3		1.6		2.1		ns
t_{WAH}	2.1		2.5		3.3		ns
t_{RASU}	2.2		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		5.1		6.4		8.4	ns
$t_{EABRCOMB}$	5.1		6.4		8.4		ns
$t_{EABRCREG}$	4.8		5.7		7.6		ns
t_{EABWP}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	6.7		8.1		10.7		ns
$t_{EABWCREG}$	6.6		8.0		10.6		ns
t_{EABDD}		4.0		5.1		6.7	ns
$t_{EABDATACO}$		0.8		1.0		1.3	ns
$t_{EABDATASU}$	1.3		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.9		1.1		1.5		ns
t_{EABWEH}	0.4		0.5		0.6		ns
$t_{EABWDSU}$	1.5		1.8		2.4		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.7		ns
t_{EABWAH}	0.4		0.5		0.7		ns
t_{EABWO}		3.4		4.4		5.8	ns

Table 63. EPF10K200E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.2		4.6		5.7	ns
t_{DIN2LE}		1.7		1.7		2.0	ns
$t_{DIN2DATA}$		1.9		2.1		3.0	ns
$t_{DCLK2IOE}$		2.5		2.9		4.0	ns
$t_{DCLK2LE}$		1.7		1.7		2.0	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.6		3.6	ns
$t_{SAMECOLUMN}$		2.5		2.7		4.1	ns
$t_{DIFFROW}$		4.8		5.3		7.7	ns
$t_{TWOROWS}$		7.1		7.9		11.3	ns
$t_{LEPERIPH}$		7.0		7.6		9.0	ns
$t_{LABCARRY}$		0.1		0.1		0.2	ns
$t_{LABCASC}$		0.9		1.0		1.4	ns

Table 71. EPF10K50S External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		8.0		9.5		12.5	ns
t_{INSU} *(2)*	2.4		2.9		3.9		ns
t_{INH} *(2)*	0.0		0.0		0.0		ns
t_{OUTCO} *(2)*	2.0	4.3	2.0	5.2	2.0	7.3	ns
t_{INSU} *(3)*	2.4		2.9				ns
t_{INH} *(3)*	0.0		0.0				ns
t_{OUTCO} *(3)*	0.5	3.3	0.5	4.1			ns
t_{PCISU}	2.4		2.9		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	7.7	–	–	ns

Table 72. EPF10K50S External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(2)*	2.7		3.2		4.3		ns
$t_{INHBIDIR}$ *(2)*	0.0		0.0		0.0		ns
$t_{INHBIDIR}$ *(3)*	0.0		0.0		–		ns
$t_{INSUBIDIR}$ *(3)*	3.7		4.2		–		ns
$t_{OUTCOBIDIR}$ *(2)*	2.0	4.5	2.0	5.2	2.0	7.3	ns
$t_{XZBIDIR}$ *(2)*		6.8		7.8		10.1	ns
$t_{ZXBIDIR}$ *(2)*		6.8		7.8		10.1	ns
$t_{OUTCOBIDIR}$ *(3)*	0.5	3.5	0.5	4.2	–	–	
$t_{XZBIDIR}$ *(3)*		6.8		8.4		–	ns
$t_{ZXBIDIR}$ *(3)*		6.8		8.4		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30.
(2) This parameter is measured without use of the ClockLock or ClockBoost circuits.
(3) This parameter is measured with use of the ClockLock or ClockBoost circuits

Table 74. EPF10K200S Device IOE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ZX2}		4.5		4.8		6.6	ns
t_{ZX3}		6.6		7.6		10.1	ns
t_{INREG}		3.7		5.7		7.7	ns
t_{IOFD}		1.8		3.4		4.0	ns
t_{INCOMB}		1.8		3.4		4.0	ns

Table 75. EPF10K200S Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.8		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.1		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABBYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.7		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		2.1		3.7		4.9	ns
t_{WP}	2.1		4.0		5.3		ns
t_{RP}	1.1		1.1		1.5		ns
t_{WDSU}	0.5		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.1		1.6		2.1		ns
t_{WAH}	1.6		2.5		3.3		ns
t_{RASU}	1.6		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.1		2.8		3.8		ns

Table 77. EPF10K200S Device Interconnect Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{LABCASC}$		0.5		1.0		1.4	ns

Table 78. EPF10K200S External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(2)*	3.1		3.7		4.7		ns
t_{INH} *(2)*	0.0		0.0		0.0		ns
t_{OUTCO} *(2)*	2.0	3.7	2.0	4.4	2.0	6.3	ns
t_{INSU}*(3)*	2.1		2.7		–		ns
t_{INH} *(3)*	0.0		0.0		–		ns
t_{OUTCO}*(3)*	0.5	2.7	0.5	3.4	–	–	ns
t_{PCISU}	3.0		4.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	8.9	–	–	ns

Table 79. EPF10K200S External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(2)*	2.3		3.4		4.4		ns
$t_{INHBIDIR}$ *(2)*	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ *(3)*	3.3		4.4		–		ns
$t_{INHBIDIR}$ *(3)*	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ *(2)*	2.0	3.7	2.0	4.4	2.0	6.3	ns
$t_{XZBIDIR}$ *(2)*		6.9		7.6		9.2	ns
$t_{ZXBIDIR}$ *(2)*		5.9		6.6		–	ns
$t_{OUTCOBIDIR}$ *(3)*	0.5	2.7	0.5	3.4	–	–	ns
$t_{XZBIDIR}$ *(3)*		6.9		7.6		9.2	ns
$t_{ZXBIDIR}$ *(3)*		5.9		6.6		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(3) This parameter is measured with the use of the ClockLock or ClockBoost circuits.